

Abstract

Method and Apparatus for forming a film on a substrate.

This invention relates to a method and apparatus for
5 forming a film on the substrate. The method comprises
supplying to the chamber in gaseous or vapour form a
silicon containing organic compound and an oxidising agent
in the presence of a plasma to deposit a film on the
substrate and setting the film such that carbon containing
groups are retained therein. In particular embodiments the
setting is achieved by exposing the film to H₂ plasma.

Figure 1.

1000000-149260